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Onsemi

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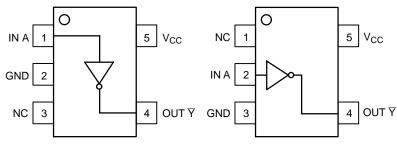
Unbuffered Inverter

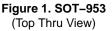
The NL17SGU04 MiniGate[™] is an advanced high–speed CMOS unbuffered inverter in ultra–small footprint.

The NL17SGU04 input structures provides protection when voltages up to 3.6 V are applied.

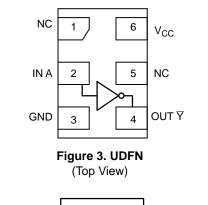
Features

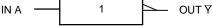
- Wide Operating V_{CC} Range: 0.9 V to 3.6 V
- High Speed: $t_{PD} = 1.9$ ns (Typ) at $V_{CC} = 3.0$ V, $C_L = 15$ pF
- Low Power Dissipation: $I_{CC} = 0.5 \ \mu A$ (Max) at $T_A = 25^{\circ}C$
- 3.6 V Overvoltage Tolerant (OVT) Input Pins
- Ultra-Small Packages
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant









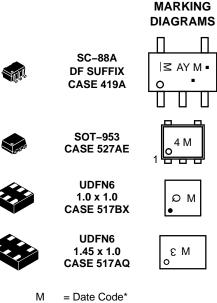






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= Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT								
	SOT-953	SC-88A	UDFN6					
1	IN A	NC	NC					
2	GND	IN A	IN A					
3	NC	GND	GND					
4	OUT Y	OUT Y	OUT Y					
5	V _{CC}	V _{CC}	NC					
6			V _{CC}					

FUNCTION TABLE

A Input	Y Output
L	Н
Н	L

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parame	ter	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +4.6	V
V _{IN}	DC Input Voltage		–0.5 to +4.6	V
V _{OUT}	DC Output Voltage	Output at High or Low State Power–Down Mode ($V_{CC} = 0 V$)	–0.5 to V _{CC} +0.5 –0.5 to +4.6	V
I _{IK}	DC Input Diode Current	V _{IN} < GND	-20	mA
Ι _{ΟΚ}	DC Output Diode Current	V _{OUT} < GND	-20	mA
I _{OUT}	DC Output Source/Sink Current		±20	mA
I _{CC}	DC Supply Current per Supply Pin		±20	mA
I _{GND}	DC Ground Current per Ground Pin		±20	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Second	econds	260	°C
TJ	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3)	>2000 >150	V
ILATCHUP	Latchup Performance Abov	e V _{CC} and Below GND at 125°C (Note 4)	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
Tested to EIA/JESD22-A114-A.
Tested to EIA/JESD22-A115-A.

4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	0.9	3.6	V
V _{IN}	Digital Input Voltage	0.0	3.6	V
V _{OUT}	Output Voltage Output at High or Low State Power–Down Mode (V _{CC} = 0 V	e 0.0) 0.0	V _{CC} 3.6	V
T _A	Operating Temperature Range	-55	+125	°C
Δt / ΔV	Input Transition Rise or Fail Rate $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	′ 0	10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

					T _A = 25°C		7⊿T 55°C to	∖ = o +125°C	
Symbol	Parameter	C	onditions	V _{CC} (V)	Min	Max	Min	Max	Unit
VIH	High-Level Input			0.9	V _{CC}		V _{CC}		V
	Voltage			1.1 to 1.3	0.7xV _{CC}		0.7xV _{CC}		1
				1.4 to 1.6	$0.65 \mathrm{xV}_{\mathrm{CC}}$		$0.65 \mathrm{xV}_{\mathrm{CC}}$		1
				1.65 to 1.95	$0.65 \mathrm{xV}_{\mathrm{CC}}$		$0.65 \mathrm{xV}_{\mathrm{CC}}$		1
				2.3 to 2.7	1.7		1.7		
				3.0 to 3.6	2.0		2.0		
VIL	Low-Level Input			0.9		GND		GND	V
	Voltage			1.1 to 1.3		0.3xV _{CC}		0.3xV _{CC}	
				1.4 to 1.6		0.35xV _{CC}		0.35xV _{CC}	1
				1.65 to 1.95		0.35xV _{CC}		0.35xV _{CC}	
				2.3 to 2.7		0.7		0.7	1
				3.0 to 3.6		0.8		0.8	1
V _{OH}	High-Level	V _{IN} =	I _{OH} = -20 μA	0.9	0.75		0.75		V
	Output Voltage	V _{IH} or V _{IL}	I _{OH} = -0.3 mA	1.1 to 1.3	$0.75 \mathrm{xV}_{\mathrm{CC}}$		$0.75 \mathrm{xV}_{\mathrm{CC}}$		
			I _{OH} = -1.7 mA	1.4 to 1.6	$0.75 \mathrm{xV}_{\mathrm{CC}}$		$0.75 \mathrm{xV}_{\mathrm{CC}}$		
			I _{OH} = -3.0 mA	1.65 to 1.95	Vcc-0.45		Vcc-0.45		1
			I _{OH} = -4.0 mA	2.3 to 2.7	2.0		2.0		1
			I _{OH} = -8.0 mA	3.0 to 3.6	2.48		2.48		1
V _{OL}	Low-Level	V _{IN} =	I _{OL} = 20 μA	0.9		0.1		0.1	V
	Output Voltage	V _{IH} or V _{IL}	I _{OL} = 0.3 mA	1.1 to 1.3		0.25xV _{CC}		0.25xV _{CC}	
			I _{OL} = 1.7 mA	1.4 to 1.6		0.25xV _{CC}		0.25xV _{CC}	1
			I _{OL} = 3.0 mA	1.65 to 1.95		0.45		0.45	1
			I _{OL} = 4.0 mA	2.3 to 2.7		0.4		0.4	1
			I _{OL} = 8.0 mA	3.0 to 3.6		0.4		0.4	1
I _{IN}	Input Leakage Current	0 ≤	$V_{IN} \leq 3.6 V$	0 to 3.6		±0.1		±1.0	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} =	V_{CC} or GND	3.6		0.5		10.0	μΑ

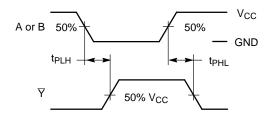
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Symbol	Parameter	Test Condition	V _{CC} (V)	-	T _A = 25° (;	T _A -55°C to	= +125°C	
				Min	Тур	Max	Min	Max	Unit
t _{PLH} ,	Propagation Delay,	$C_{L} = 10 \text{ pF},$	0.9	-	8.0	10.3	-	13.3	ns
t _{PHL}	A to Y	$R_L = 1 M\Omega$	1.1 to 1.3	-	6.0	9.4	-	12.2	
			1.4 to 1.6	-	3.2	8.5	-	10.0	
			1.65 to 1.95	-	2.6	6.2	-	6.7	
			2.3 to 2.7	-	2.0	3.9	-	4.4	
			3.0 to 3.6	-	1.7	3.1	-	3.7	
		$C_{L} = 15 \text{ pF},$	0.9	-	19.5	11.7	-	14.5	ns
		$\bar{R_L} = 1 M\Omega$	1.1 to 1.3	-	7.0	9.2	-	12.2	
			1.4 to 1.6	-	3.5	6.3	-	10.2	
			1.65 to 1.95	-	3.0	5.9	-	7.1	
			2.3 to 2.7	-	2.3	4.4	-	5.0	
			3.0 to 3.6	-	1.9	3.4	-	3.9	
		$C_L = 30 \text{ pF},$ $R_L = 1 \text{ M}\Omega$	0.9	-	10.0	12.5	-	15.6	ns
		$R_{L} = 1 MS2$	1.1 to 1.3	-	9.0	11.6	-	13.8	
			1.4 to 1.6	-	6.0	9.1	-	12.9	
			1.65 to 1.95	-	4.5	8.2	-	9.6	
			2.3 to 2.7	-	3.2	5.7	-	6.1	
			3.0 to 3.6	-	2.5	4.4	-	4.8	
C _{IN}	Input Capacitance		0 to 3.6		3	-	-	-	pF
C _O	Output Capacitance	V _O = GND	0		3	-	-	-	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	f = 10 MHz	0.9 to 3.6	-	4	-	-	-	pF

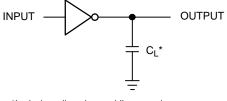
AC ELECTRICAL CHARACTERISTICS Input $t_f = t_f = 3.0$ ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product

performance may not be indicated by the Electrical Characteristics for the fisted test conditions, unless otherwise holded. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.







*Includes all probe and jig capacitances A 1–MHz square input wave is recommended for propagation delay tests.

Figure 6. Test Circuit

ORDERING INFORMATION

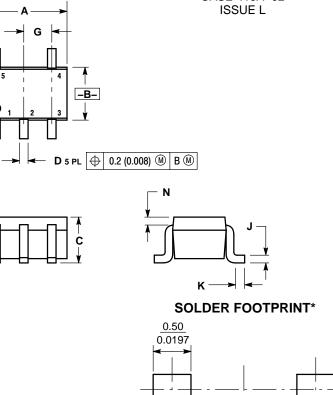
Device	Package	Shipping [†]
NL17SGU04P5T5G	SOT–953 (Pb–Free)	8000 / Tape & Reel
NL17SGU04DFT2G	SC–88A (Pb–Free)	3000 / Tape & Reel
NLV17SGU04DFT2G*	SC–88A (Pb–Free)	3000 / Tape & Reel
NL17SGU04AMUTCG (In Development)	UDFN6 1.45x1 mm (Pb-Free)	3000 / Tape & Reel
NL17SGU04CMUTCG (In Development)	UDFN6 1x1 mm (Pb-Free)	3000 / Tape & Reel
NLV17SGU04AMUTCG* (In Development)	UDFN6 1.45x1 mm (Pb-Free)	3000 / Tape & Reel
NLV17SGU04CMUTCG* (In Development)	UDFN6 1x1 mm (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

SC-88A (SC-70-5/SOT-353) CASE 419A-02



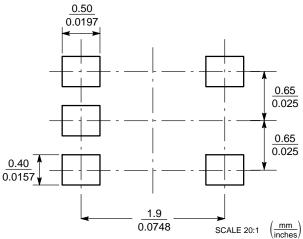
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NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BIJBPS BURRS.

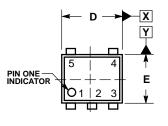
	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026	BSC	0.65 BSC		
Η		0.004		0.10	
J	0.004	0.010	0.10	0.25	
Κ	0.004	0.012	0.10	0.30	
Ν	0.008 REF		0.20	REF	
S	0.079	0.087	2.00	2.20	



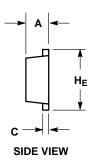
*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

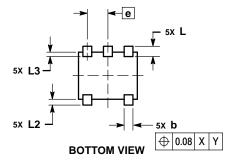
PACKAGE DIMENSIONS

SOT-953 CASE 527AE ISSUE E



TOP VIEW

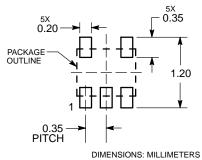




- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS				
DIM	MIN	NOM	MAX		
Α	0.34	0.37	0.40		
b	0.10	0.15	0.20		
С	0.07	0.12	0.17		
D	0.95	1.00	1.05		
E	0.75	0.80	0.85		
е		0.35 BS	С		
HE	0.95	1.00	1.05		
L	0.175 REF				
L2	0.05	0.10	0.15		
L3			0.15		

SOLDERING FOOTPRINT*

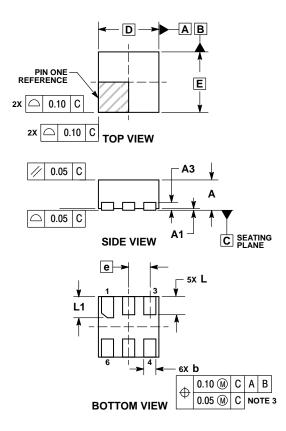


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



PACKAGE DIMENSIONS

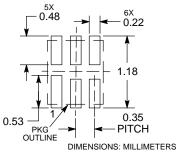
UDFN6 1.0x1.0, 0.35P CASE 517BX ISSUE O



- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP. 4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.45	0.55		
A1	0.00	0.05		
A3	0.13	REF		
b	0.12	0.22		
D	1.00	BSC		
Е	1.00	BSC		
е	0.35	BSC		
L	0.25	0.35		
L1	0.30	0.40		

RECOMMENDED SOLDERING FOOTPRINT*



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